



### SINGLE N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	l <sub>D</sub> max T <sub>A</sub> = +25°C
	7mΩ @ V <sub>GS</sub> = 10V	16A
30V	10mΩ @ V <sub>GS</sub> = 4.5V	13.5A

### Description

This MOSFET has been designed to minimize the on-state resistance (R<sub>DS(on)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

# Applications

- Backlighting
- **Power Management Functions**
- **DC-DC Converters**

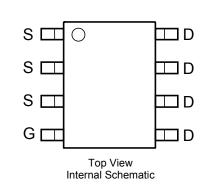
### Features and Benefits

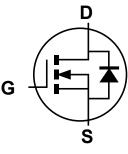
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.074 grams (approximate)







Equivalent circuit

# Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3007LSS-13	SO-8	2500/Tape & Reel

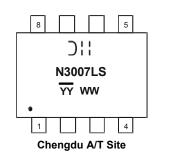
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

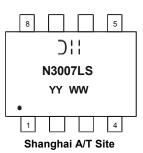
and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# Marking Information





Children Charles Constraints Constrain N3007LS = Product Type Marking Code YYWW = Date Code Marking YY or  $\overline{YY}$  = Year (ex: 13 = 2013) WW = Week (01 - 53) YY = Date Code Marking for SAT (Shanghai Assembly/ Test site) YY = Date Code Marking for CAT (Chengdu Assembly/ Test site)



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Drain Current (Note 5)	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	lo	16 13	А
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	64	A

# **Thermal Characteristics**

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	PD	2.5	W	
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	50	°C/W	
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	С°	

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	Cymbol		тур	Max	Onit		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_	_	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μA	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	—	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)				•			
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.3	_	2.1	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>		5 7.9	7 10	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 15A V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 13A	
Forward Transconductance	<b>g</b> fs	—	16.4		S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 15A	
Diode Forward Voltage	V <sub>SD</sub>	_	0.67	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 2.3A	
DYNAMIC CHARACTERISTICS (Note 8)				•			
Input Capacitance	Ciss	—	2714		pF		
Output Capacitance	Coss	_	436		pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V f = 1 0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	380	_	pF		
Gate Resistance	R <sub>G</sub>	_	0.7	_	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz	
SWITCHING CHARACTERISTICS (Note 8)	-			•			
Total Gate Charge	Qg	—	31.2 64.2	—	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 16A V <sub>DS</sub> = 15V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 16A		
Gate-Source Charge	Q <sub>gs</sub>	_	7.1	_	nC	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 16A	
Gate-Drain Charge	Q <sub>gd</sub>	_	17.1	_		V <sub>DS</sub> = 15V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 16A	
Turn-On Delay Time	t <sub>d(on)</sub>	_	10.3				
Rise Time	tr	_	14.8	_		V <sub>DS</sub> = 15V, V <sub>GS</sub> = 10V,	
Turn-Off Delay Time	t <sub>d(off)</sub>	_	85.1		ns	$I_{D} = 1A, R_{G} = 6.0\Omega$	
Fall Time	t <sub>f</sub>	_	43.6				

5.Device mounted on 2 oz. Copper pads on FR-4 PCB, with  $R_{\theta JA}$  = +50°C Notes:

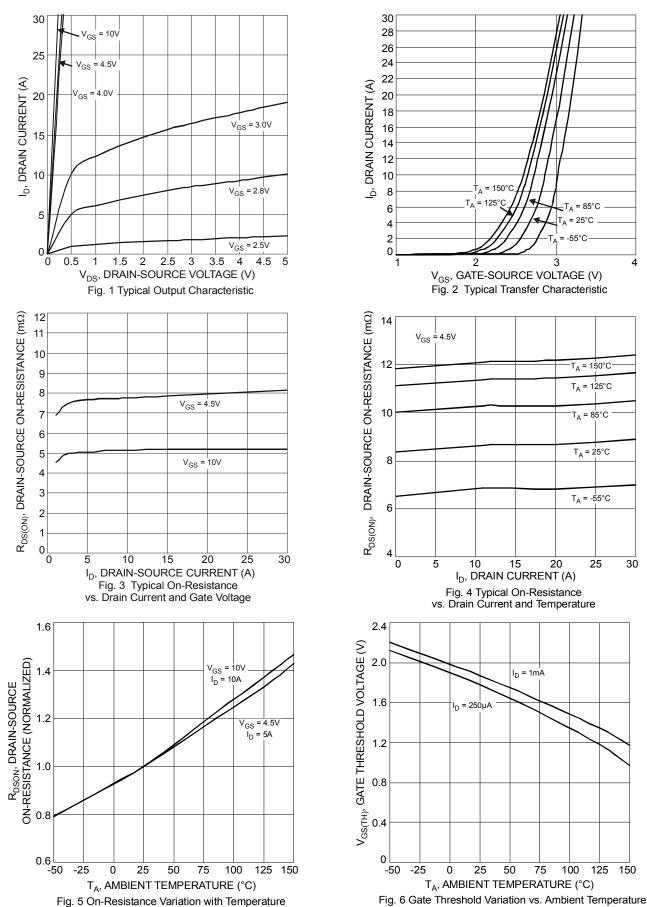
6.Pulse width ≤10µS, Duty Cycle ≤1%.
7.Short duration pulse test used to minimize self-heating effect.
8.Guaranteed by design. Not subject to product testing.





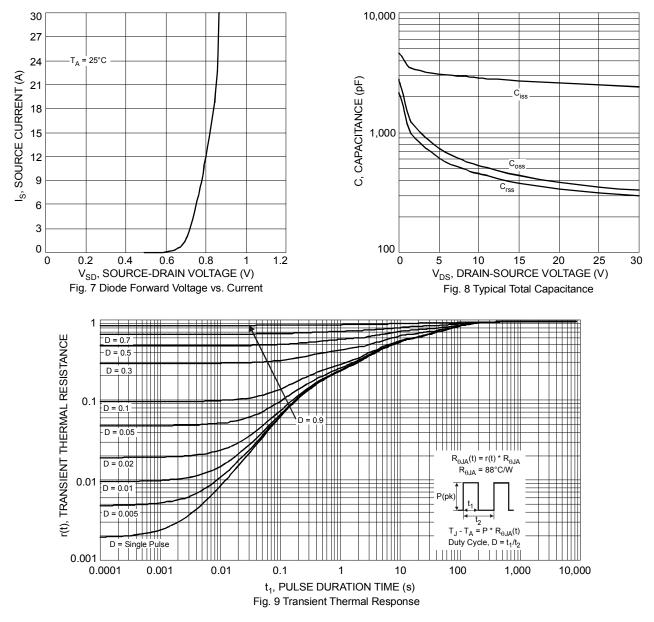
4

30



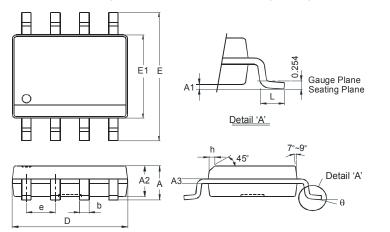


# DMN3007LSS



# **Package Outline Dimensions**





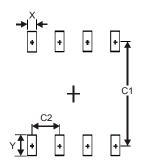
SO-8					
Dim	Min	Max			
Α	_	1.75			
A1	0.10	0.20			
A2	1.30	1.50			
A3	0.15	0.25			
b	0.3	0.5			
D	4.85	4.95			
E	5.90	6.10			
E1	3.85	3.95			
e	е 1.27 Тур				
h		0.35			
L	0.62	0.82			
θ	0°	8°			
All Dimensions in mm					

DMN3007LSS Document number: DS31460 Rev. 6 - 2



### Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Х	0.60
Y	1.55
C1	5.4
C2	1.27

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